TOSHIBA Field Effect Transistor Silicon P Channel MOS Type (U-MOSVI)

# **TPC8120**

# Lithium Ion Battery Applications Power Management Switch Applications

Unit: mm

- Small footprint due to small and thin package
- Low drain-source ON-resistance: RDS (ON) =  $2.6 \text{ m}\Omega$  (typ.)
- High forward transfer admittance:  $|Y_{fs}| = 80 \text{ S}$  (typ.)
- Low leakage current:  $IDSS = -10 \mu A (max) (VDS = -30 V)$
- Enhancement mode:  $V_{th} = -0.8 \text{ to } -2.0 \text{ V (V}_{DS} = -10 \text{ V}, I_D = -1 \text{ mA)}$

#### **Absolute Maximum Ratings (Ta = 25°C)**

Characteri	stics	Symbol	Rating	Unit	
Drain-source voltage		$V_{DSS}$	-30	V	
Drain-gate voltage (Ro	$_{\rm SS} = 20 \; \rm k\Omega)$	$V_{DGR}$	-30	V	
Gate-source voltage		$V_{GSS}$	-25/+20	V	
Drain current	DC (Note 1)	ΙD	-18	Α	
Drain current	Pulse (Note 1)	$I_{DP}$	-72	A	
Drain power dissipatio	n (t = 10 s) (Note 2a)	$P_{D}$	1.9	W	
Drain power dissipatio	n (t = 10 s) (Note 2b)	P <sub>D</sub>	1.0	W	
Single pulse avalanche	e energy (Note 3)	E <sub>AS</sub>	211	mJ	
Avalanche current		I <sub>AR</sub>	-18	Α	
Repetitive avalanche e	energy lote 2a) (Note 4)	E <sub>AR</sub>	0.03	mJ	
Channel temperature		T <sub>ch</sub>	150	°C	
Storage temperature ra	ange	T <sub>stg</sub>	-55 to 150	°C	

Note 1, Note 2, Note 3 and Note 4: See the next page.

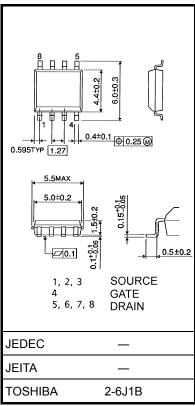
Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating

temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating

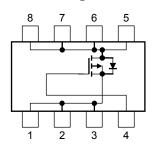
Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

This transistor is an electrostatic-sensitive device. Handle with care.



Weight: 0.080 g (typ.)

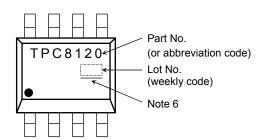
#### **Circuit Configuration**



#### **Thermal Characteristics**

Characteristics	Symbol	Max	Unit
Thermal resistance, channel to ambient (t = 10 s) (Note 2a)	R <sub>th (ch-a)</sub>	65.8	°C/W
Thermal resistance, channel to ambient (t = 10 s) (Note 2b)	R <sub>th (ch-a)</sub>	125	°C/W

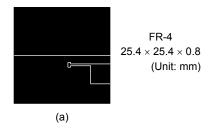
#### Marking (Note 5)

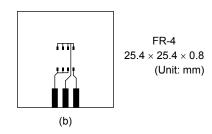


Note 6: A line under a Lot No. identifies the indication of product Labels [[G]]/RoHS COMPATIBLE or [[G]]/RoHS [[Pb]]

Please contact your TOSHIBA sales representative for details as to environmental matters such as the RoHS compatibility of Product. The RoHS is Directive 2002/95/EC of the European Parliament and of the Council of 27 January 2003 on the restriction of the use of certain hazardous substances in electrical and electronic equipment

- Note 1: Ensure that the channel temperature does not exceed 150°C.
- Note 2: (a) Device mounted on a glass-epoxy board (a)
- (b) Device mounted on a glass-epoxy board (b)





- Note 3:  $V_{DD} = -24~V$ ,  $T_{ch} = 25^{\circ}C$  (initial),  $L = 500~\mu H$ ,  $R_G = 25~\Omega$ ,  $I_{AR} = -18~A$
- Note 4: Repetitive rating: pulse width limited by maximum channel temperature

(The last digit of a year)

Note 5: • on lower left of the marking indicates Pin 1.

Weekly code: (Three digits)
 Week of manufacture
 (01 for the first week of a year: sequential number up to 52 or 53)
 Year of manufacture

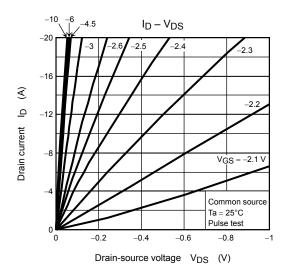
## Electrical Characteristics (Ta = 25°C)

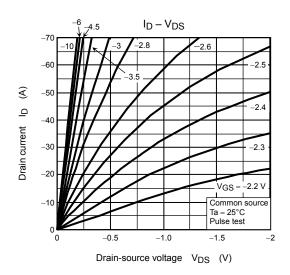
Char	acteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage curre	ent	I <sub>GSS</sub>	$V_{GS} = \pm 20 \text{ V}, V_{DS} = 0 \text{ V}$	_	_	±100	nA
Drain cut-OFF curi	rent	I <sub>DSS</sub>	$V_{DS} = -30 \text{ V}, V_{GS} = 0 \text{ V}$		_	-10	μΑ
Drain agurag brook	vdown voltago	V (BR) DSS	$I_D = -10 \text{ mA}, V_{GS} = 0 \text{ V}$		V		
Drain-source breakdown voltage		V (BR) DSX	$I_D = -10 \text{ mA}, V_{GS} = 10 \text{V (Note 7)}$	-21	_	_	_ v
Gate threshold vol	tage	V <sub>th</sub>	$V_{DS} = -10 \text{ V}, I_{D} = -1 \text{ mA}$	-0.8	_	-2.0	V
Drain agurag ON r			$V_{GS} = -4.5 \text{ V}, I_D = -9 \text{ A}$	_	3.3	4.2	- mΩ
Drain-source ON-resistance		R <sub>DS</sub> (ON)	V <sub>GS</sub> = -10 V, I <sub>D</sub> = -9 A	_	2.6	3.2	
Forward transfer a	vard transfer admittance		$V_{DS} = -10 \text{ V}, I_{D} = -9 \text{ A}$	40	80	_	S
Input capacitance		C <sub>iss</sub>	V <sub>DS</sub> = -10 V, V <sub>GS</sub> = 0 V, f = 1 MHz	_	7420	_	pF
Reverse transfer capacitance		C <sub>rss</sub>		_	1180	_	
Output capacitance		C <sub>oss</sub>		_	1440	_	
Output capacitance	Rise time	t <sub>r</sub>	Vcs	_	10	_	- ns
Cuitabing time	Turn-ON time	t <sub>on</sub>	V <sub>GS</sub> -10 V	_	18	- ±10010102.0 3	
Switching time	Fall time	t <sub>f</sub>	C	_	275	_	
	Turn-OFF time	t <sub>off</sub>		_	790	_	
Total gate charge (gate-source plus	gate-drain)	Qg	V <sub>DD</sub> ≈ -24 V, V <sub>GS</sub> = -10 V.		180		
Gate-source charge 1		Q <sub>gs1</sub>	$I_D = -18 \text{ A}$		20		nC
Gate-drain ("miller"	') charge	Q <sub>gd</sub>		_	40	_	

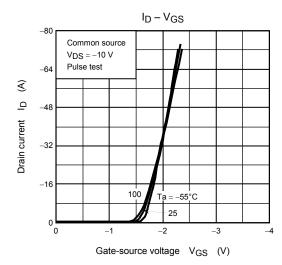
### **Source-Drain Ratings and Characteristics (Ta = 25°C)**

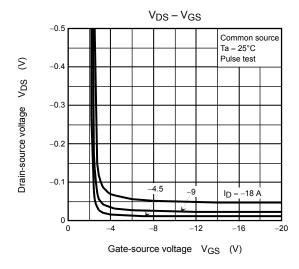
Characteristics		Symbol	Test Condition	Min	Тур.	Max	Unit	
Drain reverse current	Pulse	(Note 1)	I <sub>DRP</sub>	_	_	_	-72	Α
Forward voltage (diode)		V <sub>DSF</sub>	$I_{DR} = -18 \text{ A}, V_{GS} = 0 \text{ V}$	_	_	1.2	V	

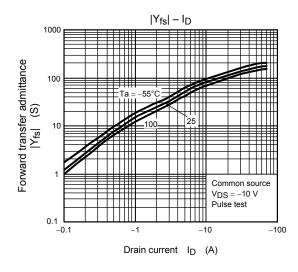
Note 7: V<sub>DSX</sub> mode (the application of a plus voltage between gate and source) may cause decrease in maximum rating of drain-source voltage.

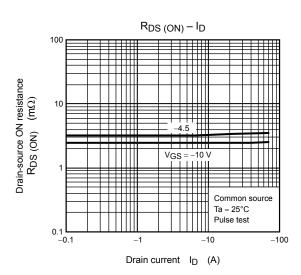


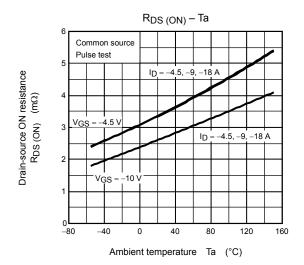


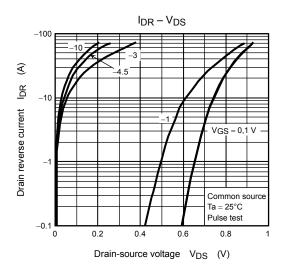


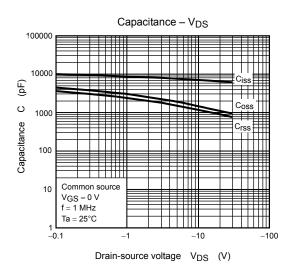


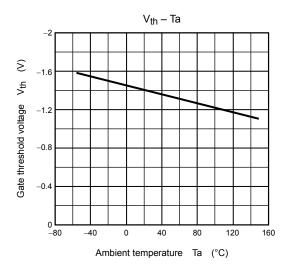


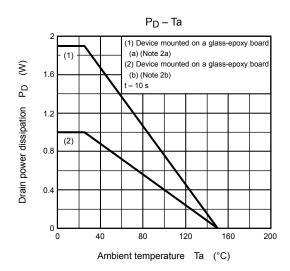


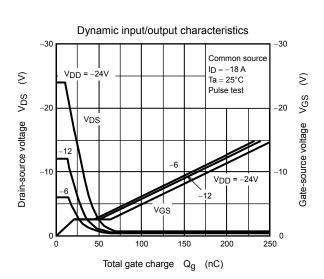


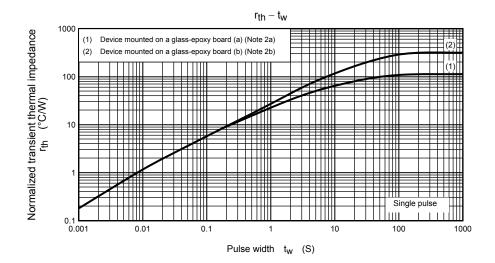


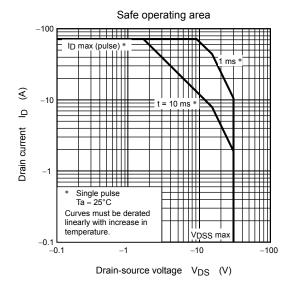












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